

**AMENDMENTS TO THE SPECIFICATION**

Please replace the paragraph beginning on page 39, line 23 with the following new paragraph:

DCS gas is supplied to the DCS buffer nozzle 44 as post-processing gas. Then, since this DCS ( $\text{SiH}_2\text{Cl}_2$ ) gas can easily form Si-F bond, F component which adheres to and remains on the wall surface of the DCS buffer nozzle 44 reacts with DCS gas and they become SiF (silicon fluoride) gas. This SiF gas is discharged from the exhaust port 16 of the reaction tube 11 through the reaction chamber 12 from the DCS buffer nozzle 44. An SiN film which is a preformed film is not intentionally formed in the DCS buffer nozzle 44 when the film is to be preformed, but since a small amount of ~~DCS gas~~  $\text{NH}_3$  radical flows into the DCS buffer nozzle 44 by the dispersion effect of gas when  $\text{NH}_3$  radical is supplied, it is conceived that a small amount of preform SiN film is formed in the DCS buffer nozzle 44. Therefore, F component which adheres to and remains on the wall surface of the DCS buffer nozzle 44 is discharged from the atmosphere in the reaction tube by the reaction with respect to these film raw materials and by encapsulation under the films.